

# 2SD1260, 2SD1260A

Silicon NPN triple diffusion planar type darlington

For power amplification

Complementary to 2SB0937, 2SB0937A

## ■ Features

- High forward current transfer ratio  $h_{FE}$
- High-speed switching
- N type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

## ■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	2SD1260	$V_{CBO}$	60	V
	2SD1260A		80	
Collector-emitter voltage (Base open)	2SD1260	$V_{CEO}$	60	V
	2SD1260A		80	
Emitter-base voltage (Collector open)	$V_{EBO}$	5	V	
Collector current	$I_C$	2	A	
Peak collector current	$I_{CP}$	4	A	
Collector power dissipation	$T_a = 25^\circ\text{C}$	$P_C$	35	W
			1.3	
Junction temperature	$T_j$	150	$^\circ\text{C}$	
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$	

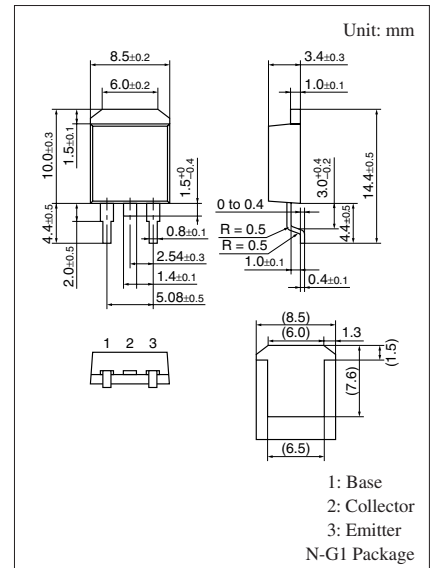
## ■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	2SD1260	$I_C = 30 \text{ mA}, I_B = 0$	60			V
	2SD1260A		80			
Base-emitter voltage	$V_{BE}$	$V_{CE} = 4 \text{ V}, I_C = 2 \text{ A}$			2.8	V
Collector-base cutoff current (Emitter open)	2SD1260	$V_{CB} = 60 \text{ V}, I_E = 0$			1	mA
	2SD1260A		$V_{CB} = 80 \text{ V}, I_E = 0$		1	
Collector-emitter cutoff current (Base open)	2SD1260	$V_{CE} = 30 \text{ V}, I_B = 0$			2	mA
	2SD1260A		$V_{CE} = 40 \text{ V}, I_B = 0$		2	
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 5 \text{ V}, I_C = 0$			2	mA
Forward current transfer ratio	$h_{FE1}$	$V_{CE} = 4 \text{ V}, I_C = 1 \text{ A}$	1000			—
	$h_{FE2}^*$	$V_{CE} = 4 \text{ V}, I_C = 2 \text{ A}$	1000		10000	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 2 \text{ A}, I_B = 8 \text{ mA}$			2.5	V
Transition frequency	$f_T$	$V_{CE} = 10 \text{ V}, I_C = 0.5 \text{ A}, f = 1 \text{ MHz}$		20		MHz
Turn-on time	$t_{on}$	$I_C = 2 \text{ A}$		0.5		$\mu\text{s}$
Storage time	$t_{stg}$	$I_{B1} = 8 \text{ mA}, I_{B2} = -8 \text{ mA}$		4.0		$\mu\text{s}$
Fall time	$t_f$	$V_{CC} = 50 \text{ V}$		1.0		$\mu\text{s}$

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

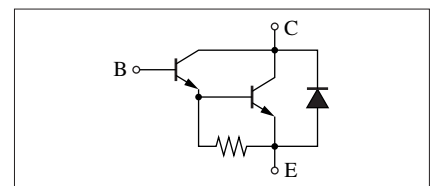
2. \*: Rank classification

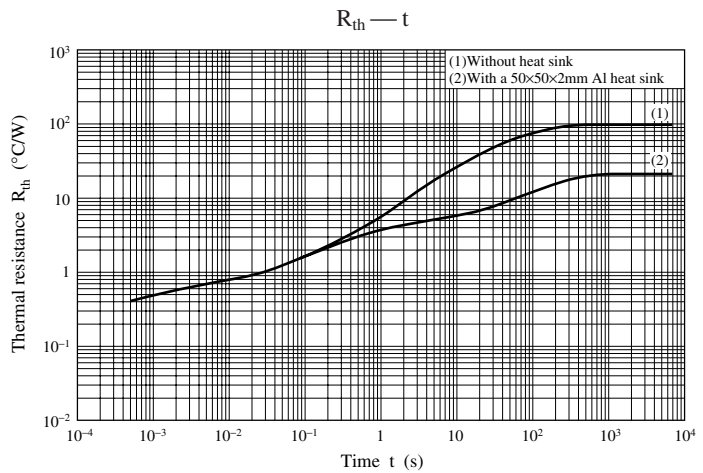
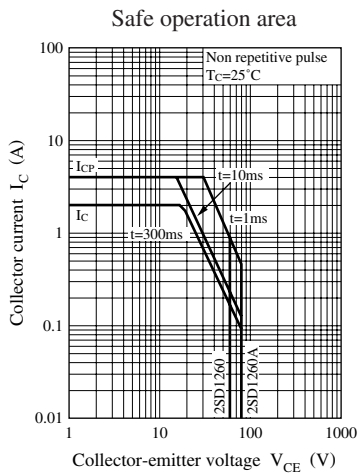
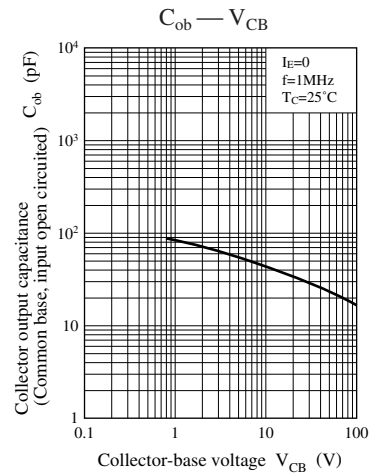
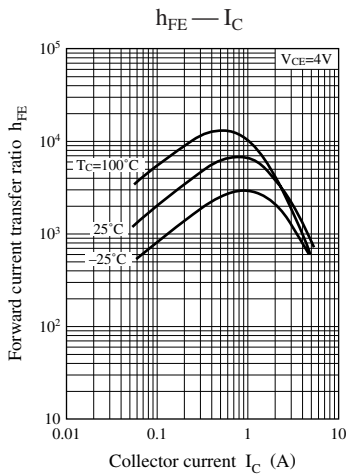
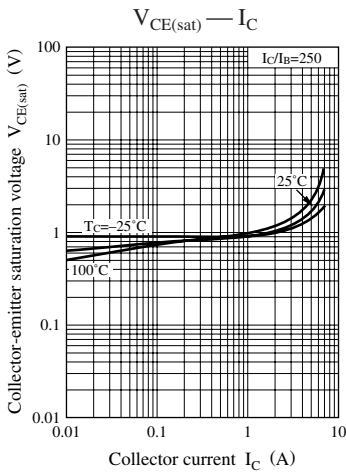
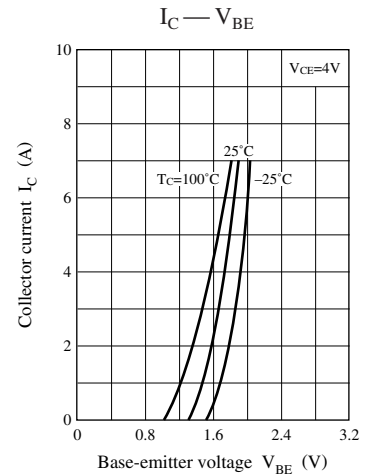
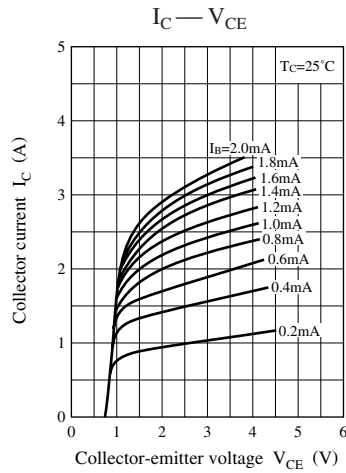
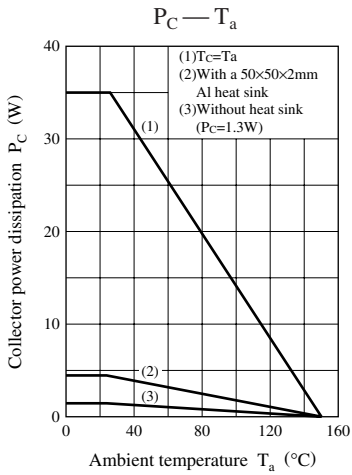
Rank	R	Q	P
$h_{FE2}$	1000 to 2500	2000 to 5000	4000 to 10000



Note) Self-supported type package is also prepared.

## Internal Connection





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